Reference number list

- 1 substrate
- 2 well area
- 5 3 buried layer
 - 4 epitaxial layer
 - 5 isolation area
 - 6 connection well
 - 7 oxide layer
- 10 8 nitride layer
 - 9 conductive electrode layer
 - 10 photoresist mask
 - 11 terminal layer
 - 12 well
- 15 13 conductive layer
 - 14 gate dielectric layer
 - 15 first gate electrode layer
 - 16 base area
 - 17 collector area
- 20 18 well
 - 19 conductive layer
 - 20 highly conductive layer
 - 20a diffusion layer
 - 21a TEOS isolation layer
- 25 21b nitride isolation layer
 - 22 second isolation layer
 - 23a ARC layer
 - 23b ARC layer
 - 24 photoresist
- 30 25 photoresist
 - 26 isolation layer
 - 27 NPN base area
 - 28 NPN collector area
 - 29 LDD area
- 35 30 first spacing layer
 - 31 second spacing layer
 - 32 HDD area
 - 33 terminal layer

- 33a diffusion area
- 34 protective layer
- 35 photoresist mask
- 36 silicon layer

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